

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>AA</i>	AA	5,976,928	11/2/99	Van Buskirk and Kirlin			
<i>AB</i>	AB	6,018,065	1/2/00	Baum, et al.			
<i>AC</i>	AC	5,911,887	6/15/99	Smith, et al.			
<i>AD</i>	AD	5,814,238	9/29/98	Ashby, et al.			
<i>AE</i>	AE	4,659,426	4/21/87	Fuller, et al.			

[illegible]

OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)		
AF	Koteki, D.E., "A Review of High Dielectric Materials for DRAM Capacitors", <i>Integ. Ferro.</i> , 1997, Vol. 16, pp. 1-19.	
AG	Jeon, et al., "Thermal Stability of Ir/Polycrystalline-Si Structure for Bottom Electrode of Integrated Ferroelectric Capacitors", <i>Appl. Physics Lett.</i> , 1997, Vol. 71(4), pp. 467-469.	
AH	Williams, et al., "Etch Rates for Micromachining Processing", <i>Journ. For Microelectromechanical Systems</i> , December 1996, Vol. 5 (4), pp. 256-269	
AI	Vugts, et al., "Si/XeF ₂ Etching-Temperature Dependence", 1996, <i>J. Vac. Sci. Tech. A</i> , Vol. 14(5), pp. 2766-2774	
AJ	P.C. Fazan, et al., "Stacked Capacitor Modules for 64 Mb DRAMs and Beyond", <i>Semiconductor Inter.</i> , 1992, Vol. 108, pp. 108-112	
AK	L. H. Parker, et al., "Ferroelectric Materials for 64Mb and 256Mb DRAMs", <i>IEEE Circuits and Devices Mag.</i> , Jan. 1990, pp. 17-26	

EXAMINER <i>W. Olson</i>	DATE CONSIDERED AA-AE 11/17/01 AF-AK 5-7-02 (<i>Am</i>)
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

[illegible]

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FOREIGN PATENT DOCUMENTS

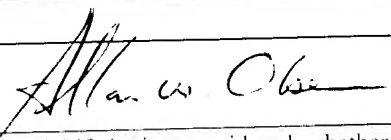
DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO

OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)

AR	Ebsworth, E.A.V., et al., "Formation of Iridium Fluoroacyl Complexes by Reaction of Iridium Carbonyls with Xenon Difluoride and Reactions of these to Generate Unusual Acyl Complexes", <i>J. Chem. Soc., Dalton Trans.</i> , 1993, ISS. 7, pp. 1031-7
AS	Blake, A.J., et al., "Novel Reaction of an Iridium Carbonyl Complex with Xenon Difluoride: The First Metal Fluoroacyl Complex", <i>J. Chem. Soc., Chem. Commun.</i> , 1988, ISS.8, pp. 529-530
AT	Sladkey, F.O., et al., "Xenon Difluoride as a Fluoride Ion Donor" <i>J. Chem. Soc. A</i> , 1969, Vol. 14, pp. 2179-88
AU	Floy I. Chang, et al., Gas-Phase Silicon Micromachining with Xenon Difluoride, <i>Proc. Of SPIE</i> vol. 2641, pp. 117-128. DUPLICATE AC on pgs 2 & 3

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